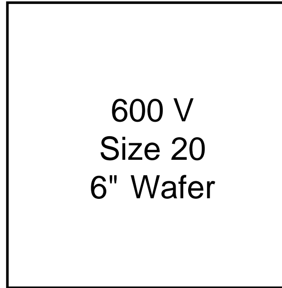
International
IOR Rectifier

Preliminary Data Sheet PD-20600 rev. C 2/04

HF20A060ACE

Hexfred Die in Wafer Form



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	1.7V Max.	T_J = 25°C, I_F = 12.0A
BV_R	Reverse Breakdown Voltage	600V Min.	T_J = 25°C, I_R = 200µA
I_{RM}	Reverse Leakage Current	10µA Max.	T_J = 25°C, V_R = 600V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1kA-4kA-6kA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.085" x 0.164"
Wafer Diameter	150mm, with std. < 100 > flat
Wafer Thickness	.015" ± .003"
Relevant Die Mechanical Dwg. Number	01-5160
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : IRGBC30MD2

Die Outline